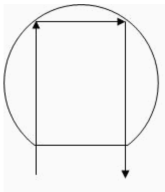
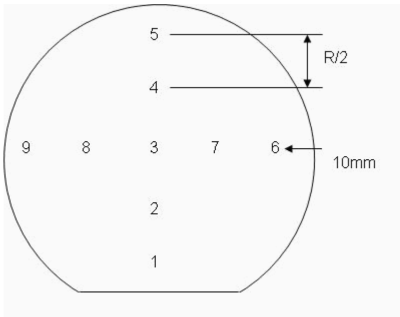
Icemos Technology Ltd **Product Specification** **1003.306601** Issue Date 19 March 2014 12:11

Part Number	Customer

Category		**Parameter**	**Specification**	**Measurement Method**
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	WaferVendor
	2.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	3.0	Primary Flat Orientation	{110}+/- 0.5 degree	Wafer Vendor
	4.0	Growth Method	CZ	Wafer Vendor
	5.0	Type	Any	Wafer Vendor
	6.0	Dopant	any	Wafer Vendor
	7.0	Resistivity	1 - 100 ohm cm	Wafer Vendor
	8.0	Overall Thickness	505.00 +/- 5.00 um	ADE, 100%
HandleSilicon	8.1	Handle Thickness	505.00 +/- 5.00 um	ADE, 100%
OverallWafer	9.0	Total Thickness Variation (TTV)	<5.00um	Guaranteed by process
	9.1	Bow	<60.00um	ADE to ASTM F534, 20%
	9.2	Warp	<60.00um	ADE to ASTM F534, 20%
	10.0	Orientation	<100> +/-0.5	Wafer Vendor
	11.0	Back Surface Quality	Polished with laser mark	Wafer Vendor
	12.0	Front Surface Quality	Prime	Wafer Vendor
	13.0	Edge Chips	None	Bright Light 100% (note 2)
DeviceSilicon	15.0	Haze	None	Bright Light, 100% (note 2).
	16.0	Scratches	None	Bright Light, 100% (note 2).

Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below:  		
Additional Information			